

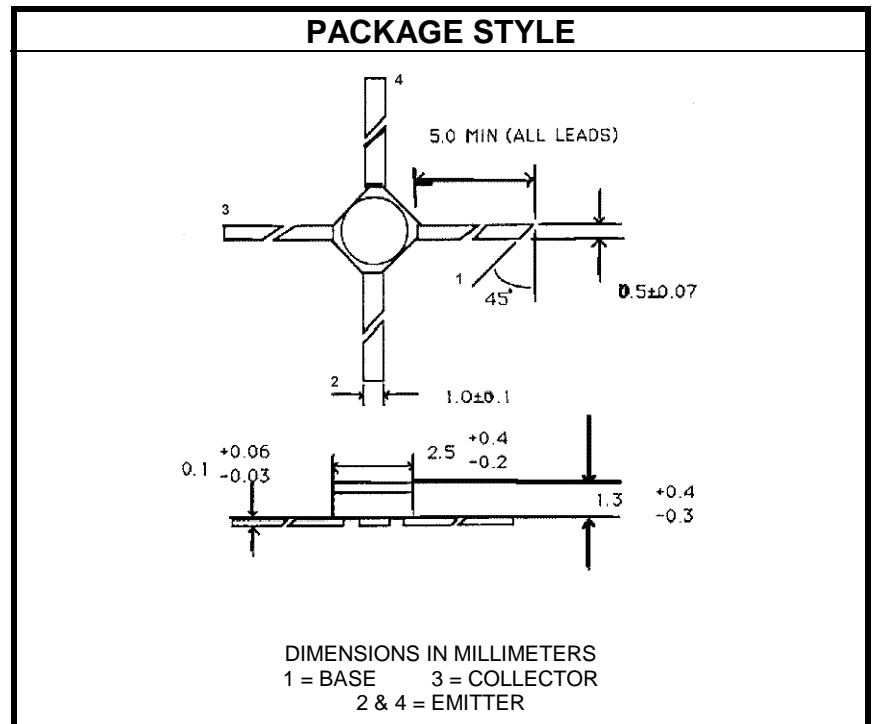
NPN SILICON RF TRANSISTOR

DESCRIPTION:

The **2SC2585** is a Common Emitter Device Designed for Low Noise Amplifier and Medium Power Oscillator Applications up to 8.5 GHz.

MAXIMUM RATINGS

I_C	65 mA
V_{CEO}	12 V
V_{CBO}	25 V
V_{EB}	1.5 V
P_T	400 mW @ $T_C = 166^\circ\text{C}$
T_J	-65°C to $+200^\circ\text{C}$
T_{STG}	-65°C to $+200^\circ\text{C}$
θ_{JC}	85°C/W



CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
I_{CBO}	$V_{CB} = 8.0\text{ V}$					100	μA
I_{EBO}	$V_{EB} = 1.0\text{ V}$					100	μA
h_{FE}	$V_{CE} = 8.0\text{ V}$	$I_C = 7.0\text{ mA}$		50	115	250	---
f_t	$V_{CE} = 8.0\text{ V}$	$I_C = 20\text{ mA}$	$f = 1.0\text{ GHz}$		8.5		GHz
C_{cb}	$V_{CB} = 10\text{ V}$		$f = 1.0\text{ MHz}$		0.2	0.6	pF
$ S_{21E} ^2$	$V_{CE} = 8.0\text{ V}$	$I_C = 20\text{ mA}$	$f = 1.0\text{ GHz}$ $f = 2.0\text{ GHz}$ $f = 4.0\text{ GHz}$	10.0	18.0 11.0 6.5		dB
G_{NF}	$V_{CE} = 8.0\text{ V}$	$I_C = 7.0\text{ mA}$	$f = 2.0\text{ GHz}$		11.0		dB
M_{AG}	$V_{CE} = 8.0\text{ V}$	$I_C = 10\text{ mA}$	$f = 2.0\text{ GHz}$ $f = 4.0\text{ GHz}$		15.0 10.0		dB
NF	$V_{CE} = 8.0\text{ V}$	$I_C = 7.0\text{ mA}$	$f = 2.0\text{ GHz}$		2.0	2.5	dB